To: Journal of Applied Physics Editorial Board
Subject: Article Submit

Dear Editors,

Enclosed with this letter you will find an electronic submission of the manuscript entitled "Features of FeB pair light-induced dissociation and repair in silicon n^+-p-p^+ structures under ultrasound loading" by Oleg Olikh, Vitaliy Kostylyov, Victor Vlasiuk, Roman Korkishko, Yaroslav Olikh, and Roman Chupryna. This paper is original and has not simultaneously in whole or in part been submitted anywhere else. No conflict of interest exists in the submission of this manuscript.

Properties of semiconducting crystals and structures are known to be determined very much by their impurity compositions. Iron is an important impurity in silicon–based integrated circuits and solar cell technology; furthermore, iron-related defects are often transformed during the operation of appropriate devices. The present manuscript focuses on the experimental investigation of the influence of ultrasound loading of silicon solar cells on dissociation and repair of iron-boron pairs. It has been observed that ultrasound leads to a decrease in the association time and the concentration of light–dissociated pairs. We believe that using ultrasound for defect engineering would be of interest to the journal's readers.

We would very much appreciate it if you would consider the manuscript for publication in the *Journal of Applied Physics*.

Sincerely yours,
Oleg Olikh and co-authors.
E-mail: olikh@univ.kiev.ua